

Teamititted herewith for filing is the Patent Application of:

Inventor: BUAN HENG LEE, TECK HONG LOW, HAI RONG WANG, TANG YING

AND ZADIG CHERNG-CHING LAM

For: N TYPE IMPURITY DOPING USING IMPLANTATION OF P2+ IONS OR AS2+ IONS



Enclosed are:

SITSES ILIOSSE

x 2 sheets of formal drawing(s).

X An assignment of the invention to Chartered Semiconductor Manufacturing, Ltd.

An associate power of attorney

The filing fee has been calculated as shown below:

•	(Col. 1)	(Col. 2)	OTHER THAN A	SMALL ENTITY
FOR:	NO. FILED	NO. EXTRA	RATE	FEE
BASIC FEE		><		\$ 790.
TOTAL CLAIMS	28 -20=	8	x 22 =	\$ 176.
INDEP CLAIMS	4 -3=	. 1	x 82 =	\$ 82.
MULTIPLE DEPENDENT CLAIM PRESENTED + 260 =				
		<u>_s</u>	UB TOTAL	\$ 1,048.
		A	SSIGNMENT	\$40.
•		l I	'OTAL	\$ 1,088.

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 $\overline{\mathbf{x}}$ Any additional filing fees required under 37 CFR §1.16.

 $\overline{\mathbf{x}}$ Any patent application processing fees under 37 CFR §1.17.

Respectfully submitted,

STEPHEN B. ACKERMAN, REG. NO. 37,761